



MAC97A6,A8 TRIAC

MAIN FEATURES

Symbol	value	unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	MAC97A6	400 V
	MAC97A8	600 V
I_{TSM}	8	A

TO-92

1. ANODE

2. GATE

3. ANODE



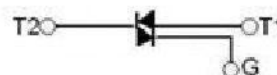
DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

FEATURES

- Blocking voltage to 400 V (MAC97A6)
- RMS on-state current to 0.6 A
- General purpose bidirectional switching

Equivalent Circuit



APPLICATIONS

- General purpose bidirectional switching
- Phase control applications
- Solid state relays

Limiting values

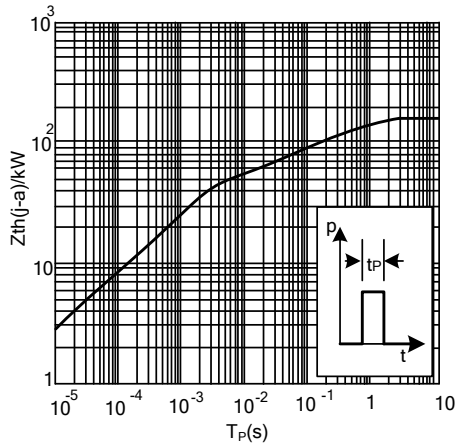
Symbol	Parameter	Conditions	Value	Unit
V_{DRM}/V_{RRM}	repetitive peak off-state voltage	MAC97A6 $T_j = 25 \text{ to } 125 \text{ }^\circ\text{C}$	400	V
		MAC97A8 $T_j = 25 \text{ to } 125 \text{ }^\circ\text{C}$	600	
I_{GM}	gate current(peak value)	$t = 2\mu\text{s max}$	1	A
V_{GM}	gate voltage(peak value)	$t = 2\mu\text{s max}$	5	V
P_{GM}	gate power(peak value)	$t = 2\mu\text{s max}$	5	W
T_j	Junction Temperature	-	-40 ~ 125	$^\circ\text{C}$
T_{stg}	Storage Temperature	-	-40 ~ 150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

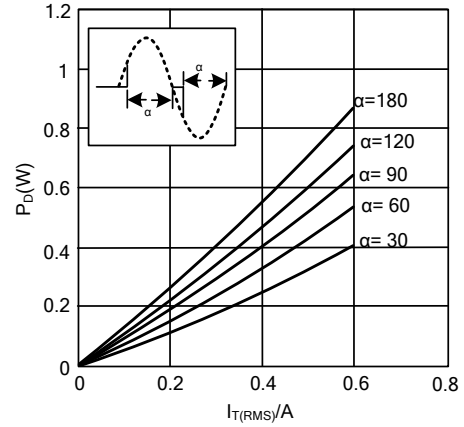
Parameter	Symbol	Test conditions	Min	Max	Unit	
Rated repetitive peak off-state/reverse voltage	V_{DRM}, V_{RRM}	$I_D=10\mu\text{A}$ MAC97A6 MAC97A8	400 600		V	
Rated repetitive peak off-state current	I_{DRM}	$V_D=V_{DRM}$		10	μA	
On-state voltage	V_{TM}	$I_T=1\text{A}, I_G=50\text{mA}$		1.9	V	
Gate trigger current	I	I_{GT}	$V_D=12\text{V}$ $R_L=100\Omega$	$T_2(+), G(+)$	5	mA
				$T_2(+), G(-)$	5	mA
				$T_2(-), G(-)$	5	mA
				$T_2(-), G(+)$	-	mA
Gate trigger voltage	I	V_{GT}	$V_D=12\text{V}$ $R_L=100\Omega$	$T_2(+), G(+)$	1.5	V
				$T_2(+), G(-)$	1.5	V
				$T_2(-), G(-)$	1.5	V
				$T_2(-), G(+)$	-	V
Holding current	I_H	$I_T=600\text{mA}, I_G=20\text{mA}$		10	mA	

■ TYPICAL CHARACTERISTICS

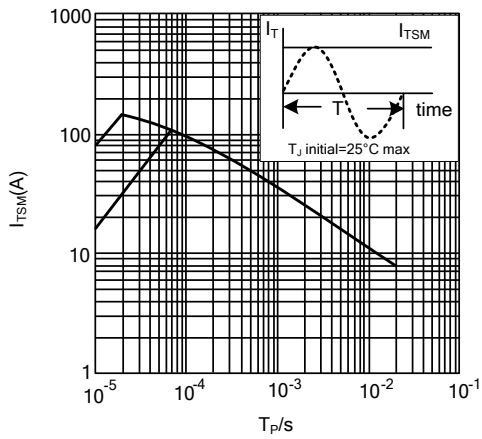
Transient Thermal Impedance From Junction to Ambient as a Function of Pulse Duration.



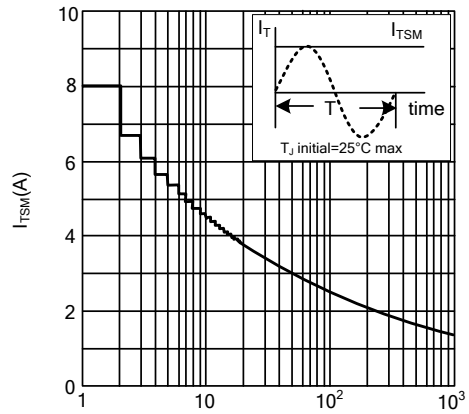
Maximum On-State Dissipation as a Function of RMS On-State Current; Typical Values. α =Conduction Angle.



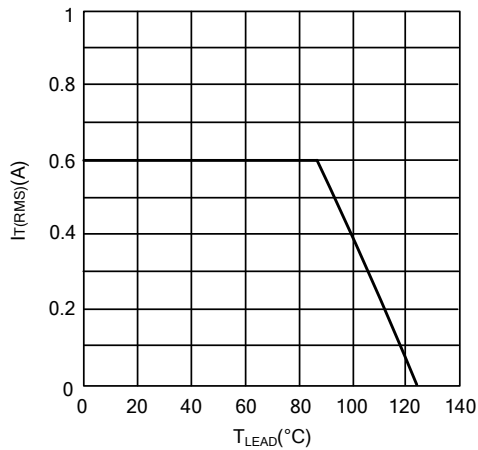
Maximum Permissible Non-Repetitive Peak on-State Current as a Function of Pulse Width for Sinusoidal Currents; Typical Values. $t_P \ll 20$ ms.



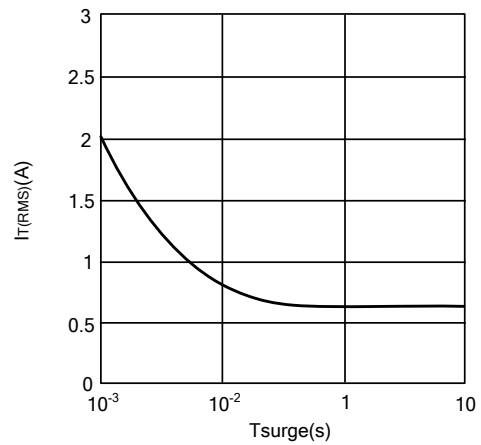
Maximum Permissible Non-Repetitive Peak On-State Current as a Function of Number of Cycles for Sinusoidal Currents; Typical Values. n=Number of Cycles at f=50Hz.



Maximum Permissible RMS Current as a Function of Lead Temperature; Typical Values.

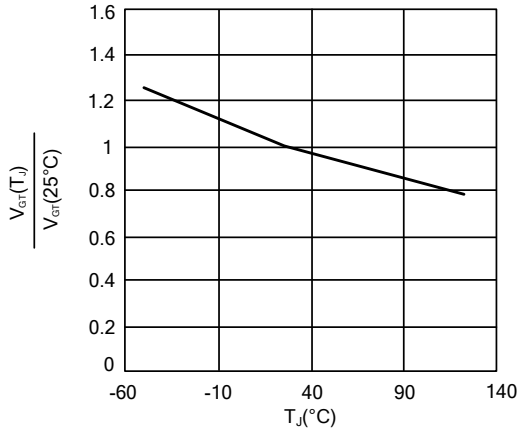


Maximum Permissible Repetitive RMS On-State Current as a Function of Surge Duration for Sinusoidal Currents; Typical Values. f=50Hz; $T_{LEAD} \ll 50^\circ\text{C}$

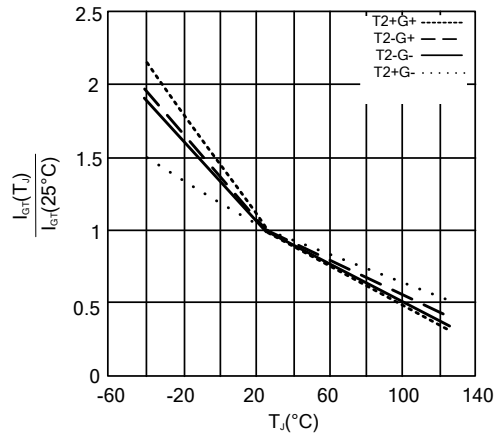


■ TYPICAL CHARACTERISTICS(Cont.)

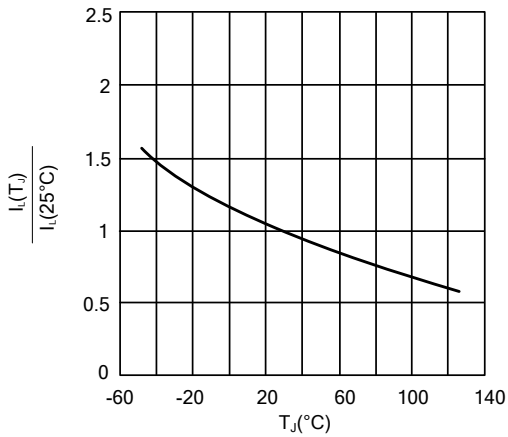
Normalized Gate Trigger Voltage as a Function of Junction Temperature; Typical Values.



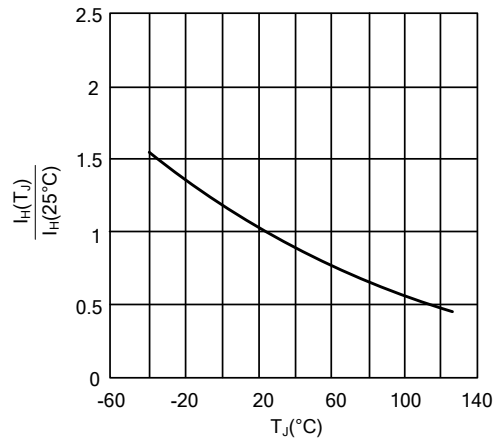
Normalized Gate Trigger Current as a Function of Junction Temperature; Typical Values.



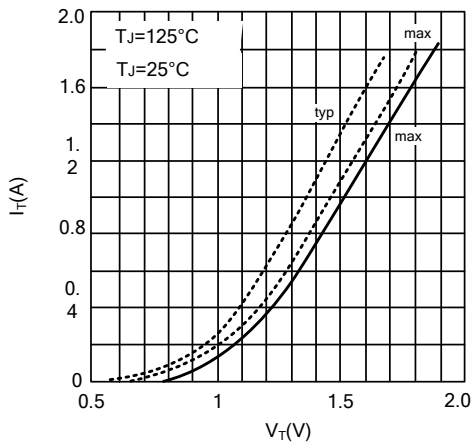
Normalized Latching Current as a Function of Junction Temperature; Typical Values.



Normalized Holding Current as a Function of Junction Temperature; Typical Values.



On-State Current as a Function of On-State Voltage; Typical and Maximum Values.



Critical Rate of Rise of Off-State Voltage as a Function of Junction Temperature; Typical Values.

